

BDW93/A/B/C

Hammer Drivers, Audio Amplifiers Applications

- Power Darlington TR
- Complement to BDW94, BDW94A, BDW94B and BDW94C respectively



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: BDW93	45	V
	: BDW93A	60	V
	: BDW93B	80	V
	: BDW93C	100	V
V _{CEO}	Collector-Emitter Voltage		
	: BDW93	45	V
	: BDW93A	60	V
	: BDW93B	80	V
	: BDW93C	100	V
I _C	Collector Current (DC)	12	А
I _{CP}	*Collector Current (Pulse)	15	А
I _B	Base Current	0.2	Α
P _C	Collector Dissipation (T _C =25°C)	80	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

Thermal Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Value	Units
$R_{\theta jc}$	Thermal Resistance	Junction to Case	1.5	°C/W

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FIACTRICAL	Characteristics T _C =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO} (sus)	* Collector-Emitter Sustaining Voltage : BDW93 : BDW93A : BDW93B : BDW93C	I _C = 100mA, I _B = 0	45 60 80 100			V V V
І _{СВО}	Collector Cut-off Current : BDW93 : BDW93A : BDW93B : BDW93C	$V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$			100 100 100 100	μΑ μΑ μΑ μΑ
I _{CEO}	Collector Cut-off Current : BDW93 : BDW93A : BDW93B : BDW93C	$V_{CE} = 45V, I_B = 0$ $V_{CE} = 60V, I_B = 0$ $V_{CE} = 80V, I_B = 0$ $V_{CE} = 100V, I_B = 0$			1 1 1	mA mA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			2	mA
h _{FE}	* DC Current Gain	$V_{CE} = 3V, I_{C} = 3A$ $V_{CE} = 3V, I_{C} = 5A$ $V_{CE} = 3V, I_{C} = 10A$	1000 750 100		20000	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = 5A$, $I_B = 20mA$ $I_C = 10A$, $I_B = 100mA$			2 3	V V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	$I_C = 5A$, $I_B = 20mA$ $I_C = 10A$, $I_B = 100mA$			2.5 4	V V
V _F	* Parallel Diode Forward Voltage	I _F = 5A I _F = 10A		1.3 1.8	2 4	V V

^{*} Pulse Test: PW=300μs, duty Cycle =1.5% Pulsed

Typical characteristics

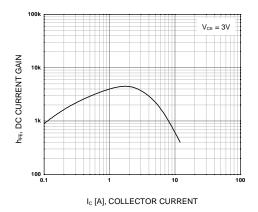


Figure 1. DC Current Gain

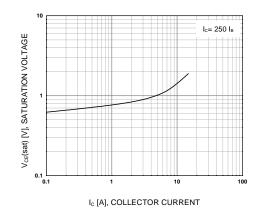


Figure 2. Collector-Emitter Saturation Voltage

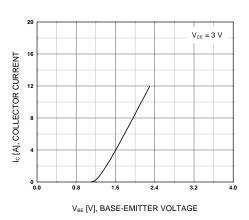


Figure 3. Base-Emitter On Voltage

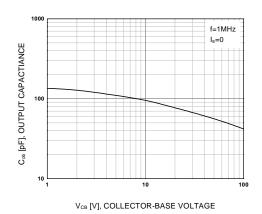


Figure 4. Collector Output Capacitance

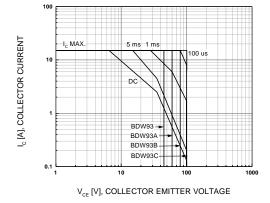


Figure 5. Safe Operating Area

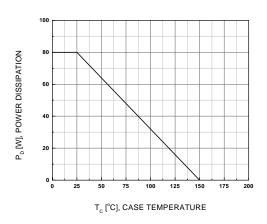
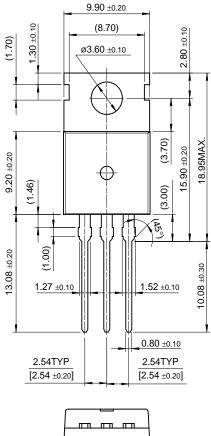


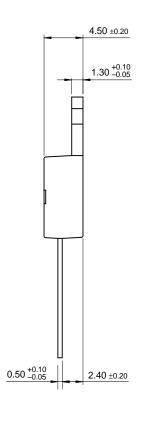
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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